

L Number	Hits	Search Text	DB	Time stamp
1	31	(fet or (field adj effect adj transistor)) with (etching adj trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 17:32
2	203	(fet or (field adj effect adj transistor)) adj trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 17:32
3	2	5512517.pn. and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 17:33
4	1	5512517.pn. and (substrate with silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 15:28
5	1259	((voltage adj supply) or signal) adj lines) and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 17:08
6	55	((voltage adj supply) or signal) adj lines) with trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 17:11
7	168	((voltage adj supply) or signal) adj lines) same trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 17:20
8	57	parallelepiped same trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 17:52
9	255	parallelepiped and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 17:25
10	10	((fet or (field adj effect adj transistor)) adj trench) and sram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 17:32
11	0	5512517.pn. and sram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 17:33
12	0	5512517.pn. and static	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 17:33
13	1	4713678.pn. and parallelepiped	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 17:54
14	1	5225697.pn. and parallelepiped	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 17:58

15	1	5225697.pn. and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 18:06
16	3	sram with (flip adj flop) with (selection adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 18:43
17	504	257/302.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 18:45
18	890	257/330.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 18:45
19	401	257/331.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/17 18:45